

(c) an auxiliary light shielding region having a size smaller than that of the first opening region, in the first opening region over the first

major surface of the mask substrate, which auxiliary light shielding region is disposed at the vertex portion of the light shielding region, and has such a size that the auxiliary light shielding region reduces deformation of the transferred pattern onto the wafer corresponding to the first opening region by reducing the light intensity on the wafer at the inner corner portion of the first opening region without affecting the whole shape of the transferred pattern onto the wafer corresponding to the first opening region; and

(d) an auxiliary opening region having a size smaller than that of the first opening region, in the light shielding region over the first major surface of the mask substrate, which auxiliary opening region is disposed at the vertex portion of the first opening region, and has such a size that the auxiliary opening region reduces deformation of the transferred pattern onto the wafer corresponding to the first opening region by enhancing the light intensity on the wafer at the outer corner portion of the first opening region without affecting the whole shape of the transferred pattern onto the

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